

ABSTRACT OF THE DISCLOSURE

An aspect of the present invention includes a first  
conductive type semiconductor region formed in a  
5 semiconductor substrate, a gate electrode formed on the first  
conductive type semiconductor region, a channel region formed  
immediately below the gate electrode in the first conductive  
type semiconductor region, and a second conductive type first  
diffusion layers constituting source/drain regions formed  
10 at opposite sides of the channel region in the first  
conductive type semiconductor region, the gate electrode  
being formed of polycrystalline silicon-germanium, in which  
the germanium concentration of at least one of the source  
side and the drain side is higher than that of the central  
15 portion.